

# AND9390/D

## 3-phase Inverter Power Module Application Note for the Compact IPM series



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### 1. Product synopsis

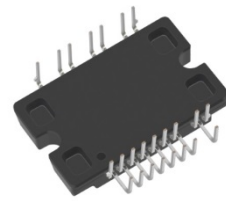
This application note provides practical guidelines for designing with the **Compact IPM series** power modules.

This series of Intelligent Power Modules (IPM) for 3-phase motor drives contains a three-phase inverter stage, gate drivers and a thermistor.

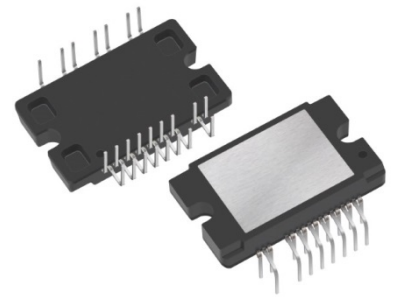
The key functions are outlined below:

- Highly integrated power module containing an inverter power stage for a high voltage 3-phase inverter in a small dual in-line (DIP) package.
- Output stage uses IGBT/FRD technology and implements Under Voltage Protection (UVP) and Over-current Protection (OCP) with a fault detection output flag. Internal bootstrap diodes are provided for the high-side drivers.
- Separate pins for each of the three low-side emitter terminals
- Thermistor for substrate temperature measurement.
- All control inputs and status outputs have voltage levels compatible with microcontrollers.
- Single  $V_{DD}$  power supply due to internal bootstrap circuit for high-side gate driver circuit.
- Mounting holes for easy assembly of heat sink with screws

### APPLICATION NOTE



DIPS



DIPS3

A simplified block diagram of a motor control system is shown in Figure 1.

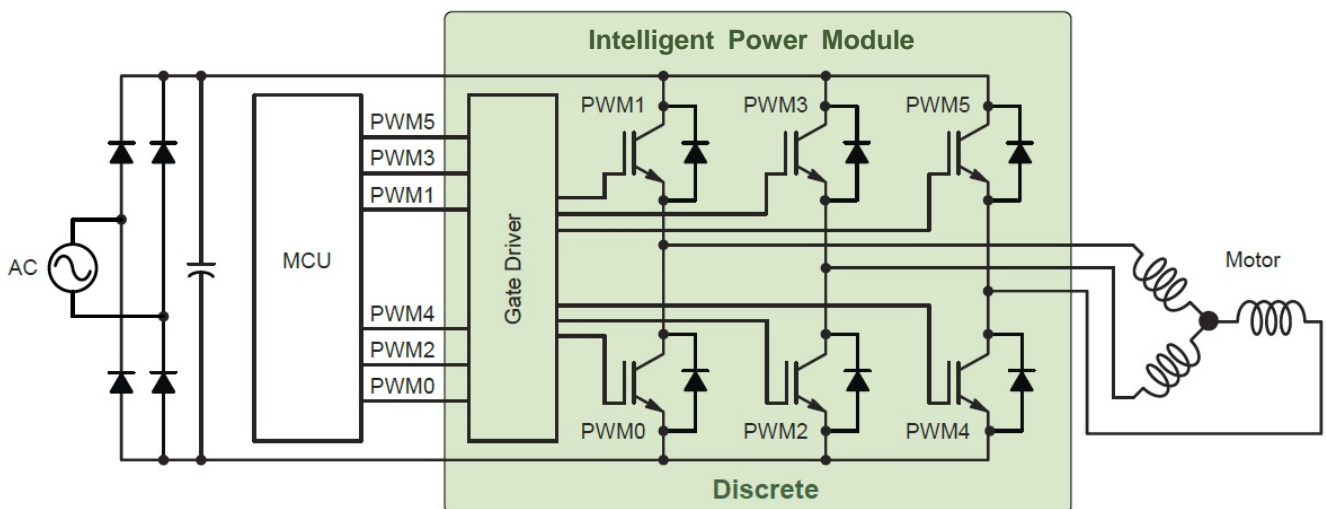


Figure 1. Motor Control System Block Diagram

## 2. Product description

Table 1 gives an overview of the available devices in the Compact IPM series. For package drawing, please refer to Chapter 6.

Device	STK5C4U332J-E	STK5Q4U340J-E *	STK5Q4U352J-E	STK5Q4U362J-E STK5Q4U363J-E	STK5Q4U395J-E *
Feature	triple shunts				
Package	DIPS	DIPS3			
Voltage (VCEmax.)	600V				
Current (Ic)	3A	5A	8A	10A	15A
Peak current (Ic)	6A	10A	16A	20A	30A
Isolation voltage	2000V				
Shunt resistance	External				

\* Under development

Table 1. Device Overview

For STK5C4U332J-E  
RCIN has internal RC network.  
Latch time is 2ms (typical).

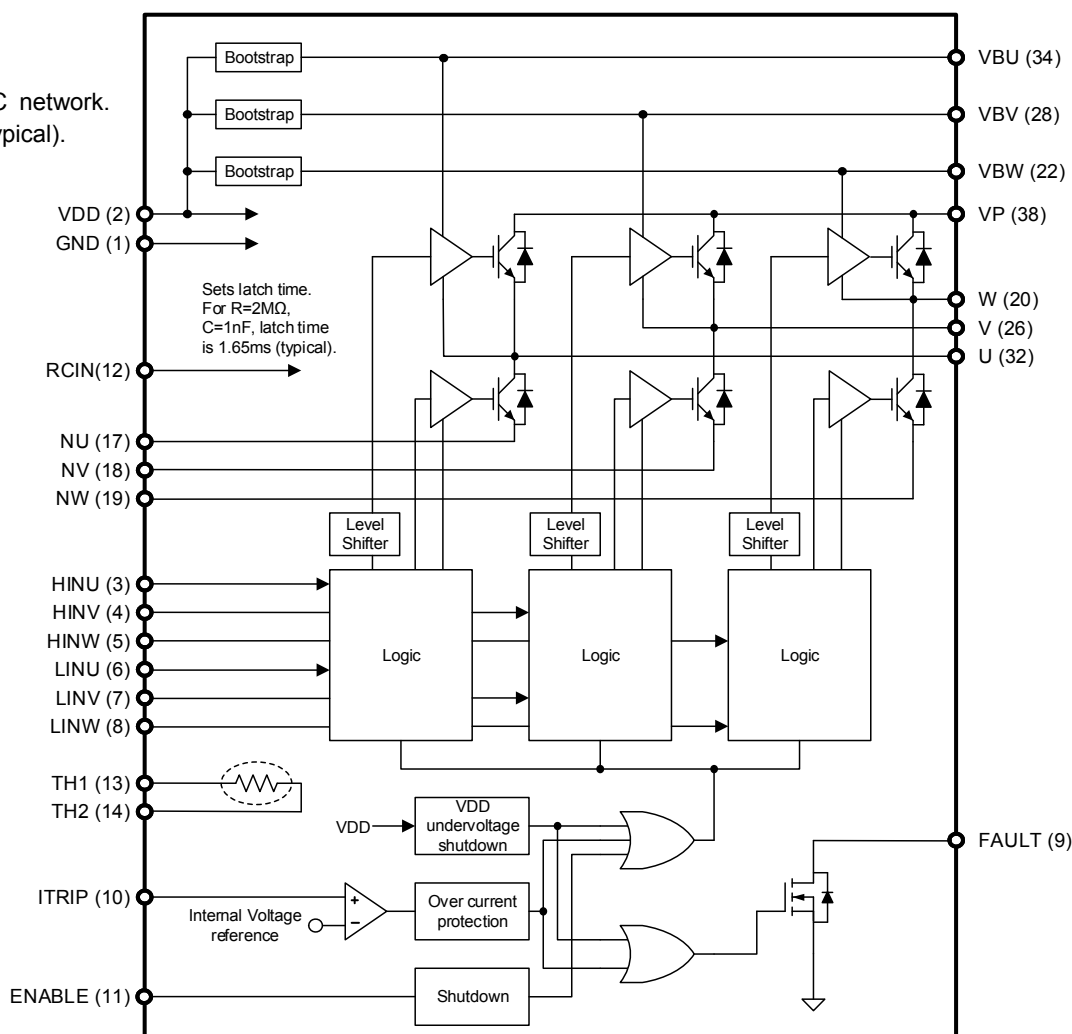


Figure 2. Compact IPM Series Internal Diagram

Three bootstrap circuits generate the voltage needed for driving the high-side IGBTs. The boost diodes are internal to the part and sourced from VDD (15V). There is an internal level shift circuit for the high-side drive signals allowing all control signals to be driven directly from GND levels common with the control circuit such as the microcontroller without requiring external isolation with optocouplers.

### 3. Performance test guidelines

The methods used to test some datasheet parameters are shown in Figures 3 to 7.

#### 3.1. Switching time definition and performance test method

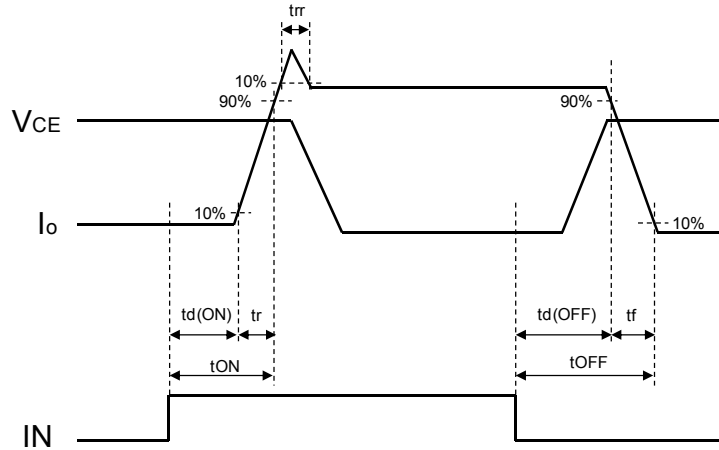


Figure 3. Switching Time Definition

Ex) Low side U phase

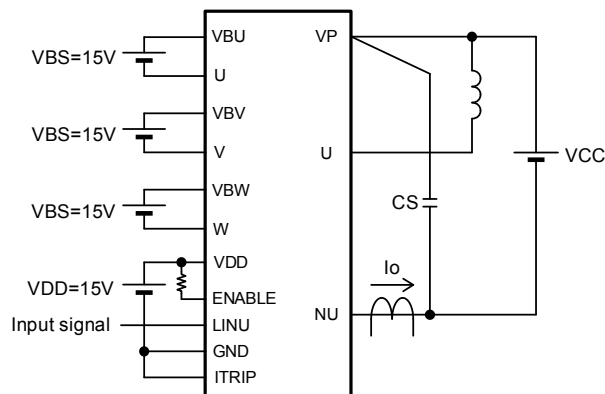


Figure 4. Evaluation Circuit (Inductive load)

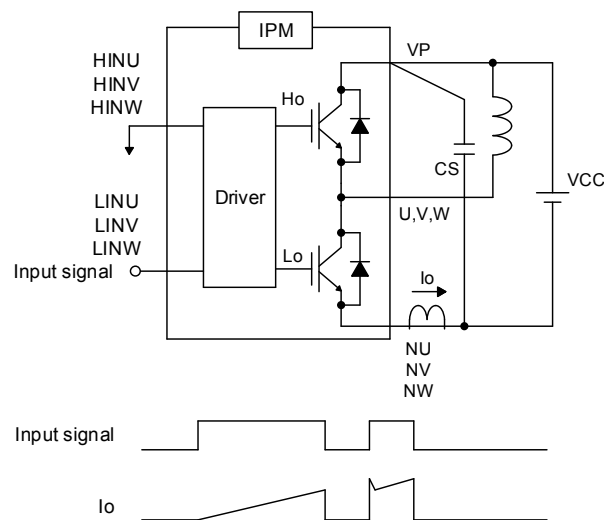


Figure 5. Switching Loss Measurement Circuit

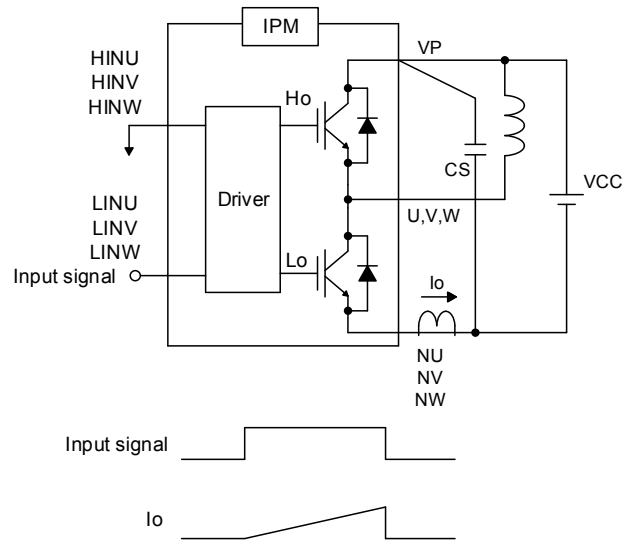


Figure 6. Reverse Bias Safe Operating Area Measurement Circuit

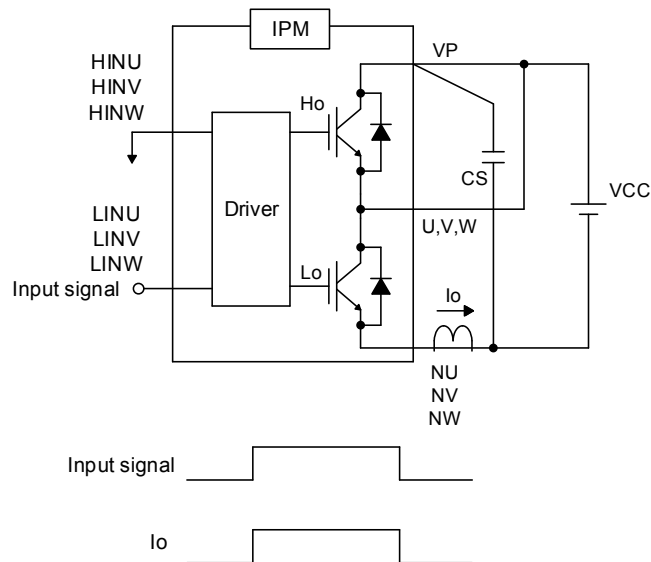


Figure 7. Short Circuit Safe Operating Area Measurement Circuit

### 3.2. Thermistor Characteristics

The TH1 and TH2 pins are connected to a thermistor mounted on the module substrate. The thermistor is used to sense the internal substrate temperature. It has the following characteristics.

Parameter	Symbol	Condition	Min	Typ.	Max	Unit
Resistance	$R_{25}$	$T_c=25^{\circ}\text{C}$	99	100	101	$\text{k}\Omega$
Resistance	$R_{100}$	$T_c=100^{\circ}\text{C}$	5.18	5.38	5.60	$\text{k}\Omega$
Temperature Range			-40		+125	$^{\circ}\text{C}$

Table 2. NTC Thermistor Specification

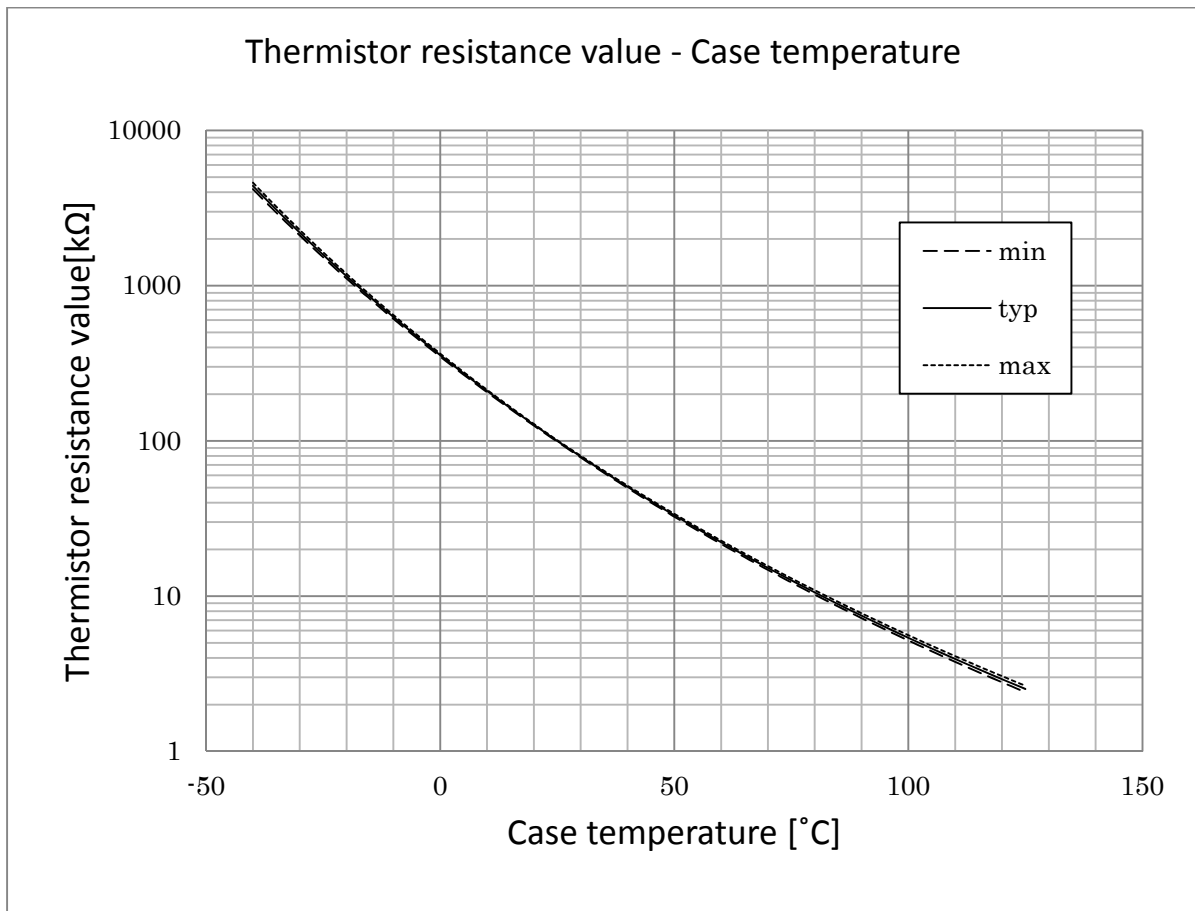


Figure 8. NTC Thermistor Resistance versus Temperature

# AND9390/D

Tc [°C]	Resistance value [kΩ]		
	Min	Typ	Max
-40	4191.52	4397.12	4612.34
-39	3904.30	4092.87	4290.13
-38	3638.69	3811.72	3992.58
-37	3392.92	3551.75	3717.65
-36	3165.38	3311.24	3463.47
-35	2954.60	3088.60	3228.35
-34	2759.25	2882.40	3010.74
-33	2578.10	2691.31	2809.21
-32	2410.02	2514.14	2622.49
-31	2253.99	2349.78	2449.39
-30	2109.07	2197.23	2288.84
-29	1974.40	2055.56	2139.84
-28	1849.20	1923.93	2001.49
-27	1732.73	1801.57	1872.97
-26	1624.34	1687.77	1753.51
-25	1523.41	1581.88	1642.43
-24	1429.20	1483.10	1538.88
-23	1341.42	1391.11	1442.51
-22	1259.58	1305.41	1352.78
-21	1183.25	1225.53	1269.20
-20	1112.02	1151.04	1191.30
-19	1045.53	1081.54	1118.67
-18	983.42	1016.66	1050.92
-17	925.39	956.08	987.69
-16	871.14	899.48	928.65
-15	820.40	846.58	873.51
-14	772.93	797.11	821.97
-13	728.49	750.83	773.79
-12	686.88	707.52	728.72
-11	647.89	666.97	686.55
-10	611.35	628.99	647.07
-9	577.04	593.34	610.04
-8	544.86	559.93	575.36
-7	514.67	528.60	542.85
-6	486.34	499.21	512.38
-5	459.73	471.63	483.79
-4	434.77	445.77	457.01
-3	411.31	421.48	431.86
-2	389.25	398.65	408.25
-1	368.50	377.19	386.06
0	348.97	357.01	365.20
1	330.58	338.01	345.57
2	313.25	320.12	327.11
3	296.94	303.29	309.74
4	281.57	287.43	293.39
5	267.08	272.50	278.00
6	253.42	258.43	263.50
7	240.54	245.16	249.84
8	228.39	232.65	236.97
9	216.91	220.85	224.83
10	206.08	209.71	213.38
11	195.85	199.20	202.58
12	186.18	189.27	192.38
13	177.05	179.89	182.76
14	168.41	171.03	173.67
15	160.24	162.65	165.08

Tc [°C]	Resistance value [kΩ]		
	Min	Typ	Max
16	152.51	154.73	156.96
17	145.20	147.23	149.28
18	138.27	140.14	142.02
19	131.72	133.43	135.16
20	125.51	127.08	128.66
21	119.63	121.07	122.51
22	114.05	115.37	116.69
23	108.77	109.97	111.17
24	103.75	104.85	105.95
25	99.00	100.00	101.00
26	94.40	95.40	96.40
27	90.04	91.03	92.03
28	85.90	86.89	87.88
29	81.97	82.96	83.94
30	78.25	79.22	80.20
31	74.71	75.68	76.65
32	71.35	72.31	73.27
33	68.16	69.10	70.05
34	65.13	66.06	67.00
35	62.25	63.17	64.09
36	59.51	60.42	61.33
37	56.91	57.80	58.70
38	54.43	55.31	56.19
39	52.07	52.93	53.80
40	49.83	50.68	51.53
41	47.70	48.53	49.37
42	45.67	46.48	47.31
43	43.73	44.53	45.34
44	41.89	42.67	43.47
45	40.13	40.90	41.68
46	38.46	39.21	39.98
47	36.86	37.60	38.35
48	35.34	36.06	36.80
49	33.89	34.60	35.31
50	32.50	33.19	33.90
51	31.18	31.86	32.55
52	29.92	30.58	31.26
53	28.72	29.37	30.03
54	27.57	28.20	28.85
55	26.47	27.09	27.72
56	25.42	26.03	26.64
57	24.42	25.01	25.62
58	23.46	24.04	24.63
59	22.55	23.11	23.69
60	21.67	22.22	22.79
61	20.84	21.37	21.92
62	20.04	20.56	21.10
63	19.27	19.78	20.31
64	18.54	19.04	19.55
65	17.83	18.32	18.82
66	17.16	17.64	18.13
67	16.52	16.99	17.46
68	15.91	16.36	16.83
69	15.32	15.76	16.21
70	14.75	15.18	15.63
71	14.21	14.63	15.06

Tc [°C]	Resistance value [kΩ]		
	Min	Typ	Max
72	13.69	14.10	14.52
73	13.19	13.59	14.00
74	12.71	13.10	13.51
75	12.25	12.64	13.03
76	11.81	12.19	12.57
77	11.39	11.76	12.13
78	10.99	11.34	11.71
79	10.60	10.95	11.30
80	10.23	10.57	10.91
81	9.87	10.20	10.54
82	9.53	9.85	10.18
83	9.20	9.51	9.83
84	8.88	9.18	9.50
85	8.57	8.87	9.18
86	8.28	8.57	8.87
87	8.00	8.28	8.58
88	7.73	8.01	8.29
89	7.47	7.74	8.02
90	7.22	7.48	7.75
91	6.98	7.23	7.50
92	6.75	7.00	7.26
93	6.52	6.77	7.02
94	6.31	6.55	6.80
95	6.10	6.34	6.58
96	5.90	6.13	6.37
97	5.71	5.93	6.17
98	5.53	5.74	5.97
99	5.35	5.56	5.78
100	5.18	5.38	5.60
101	5.01	5.21	5.42
102	4.85	5.05	5.26
103	4.70	4.89	5.09
104	4.55	4.74	4.94
105	4.41	4.59	4.79
106	4.27	4.45	4.64
107	4.14	4.32	4.50
108	4.01	4.18	4.36
109	3.89	4.06	4.23
110	3.77	3.93	4.10
111	3.66	3.82	3.98
112	3.55	3.70	3.86
113	3.44	3.59	3.75
114	3.33	3.48	3.64
115	3.24	3.38	3.53
116	3.14	3.28	3.43
117	3.05	3.19	3.33
118	2.96	3.09	3.23
119	2.87	3.00	3.14
120	2.79	2.92	3.05
121	2.71	2.83	2.96
122	2.63	2.75	2.88
123	2.55	2.67	2.80
124	2.48	2.60	2.72
125	2.41	2.52	2.64

Table 3. NTC Thermistor Resistance Values

## 4. Protection functions

This chapter describes the protection functions.

- Over-current protection
- Short circuit protection
- Under voltage lockout (UVLO) protection
- Cross conduction prevention

### 4.1. Over-current protection

Compact IPM series modules use an external shunt resistor for the OCP functionality. As shown in Figure 9, the emitters of all three low-side IGBTs are brought out to module pins. The external OCP circuit consists of a shunt resistor and a RC filter network. If the application uses three separate shunts, an op-amp circuit is used to monitor the three separate shunts and provide an over-current signal.

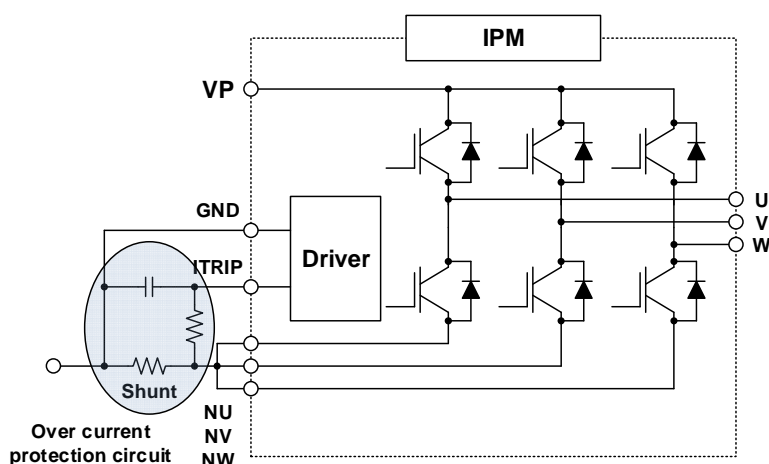


Figure 9. Over-current Protection Circuit

The OCP function is implemented by comparing the ITRIP input voltage with an internal reference voltage of 0.49V (typ). If the voltage on this terminal exceeds the trip level, an OCP fault is triggered. This voltage is the same as the voltage across the shunt resistor.

**Note:** The current value of the OCP needs to be set by correctly sizing the external shunt resistor to less than the module's maximum current rating.

When an OCP fault is detected, all internal gate drive signals for the IGBTs become inactive and the fault signal output is activated. The FAULT signal has an open drain output, so when there is a fault, the output is pulled low.

A RC filter is used on the ITRIP input to prevent an erroneous OCP detection due to normal switching noise or recovery diode current. The time constant of that RC filter should be set to a value between 1.5 $\mu$ s to 2 $\mu$ s. In any case the time constant must be shorter than the IGBTs short current safe operating area (SCSOA). Please refer to Data Sheet for SCSOA. The resulting OCP level due to the filter time constant is shown in Figure 10.

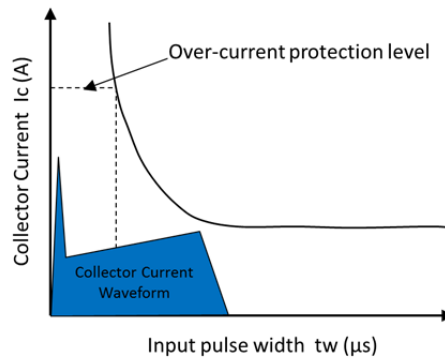


Figure 10. Filter Time Constant

For optimal performance all traces around the shunt resistor need to be kept as short as possible.

Figure 11 shows the sequence of events in case of an OCP event.

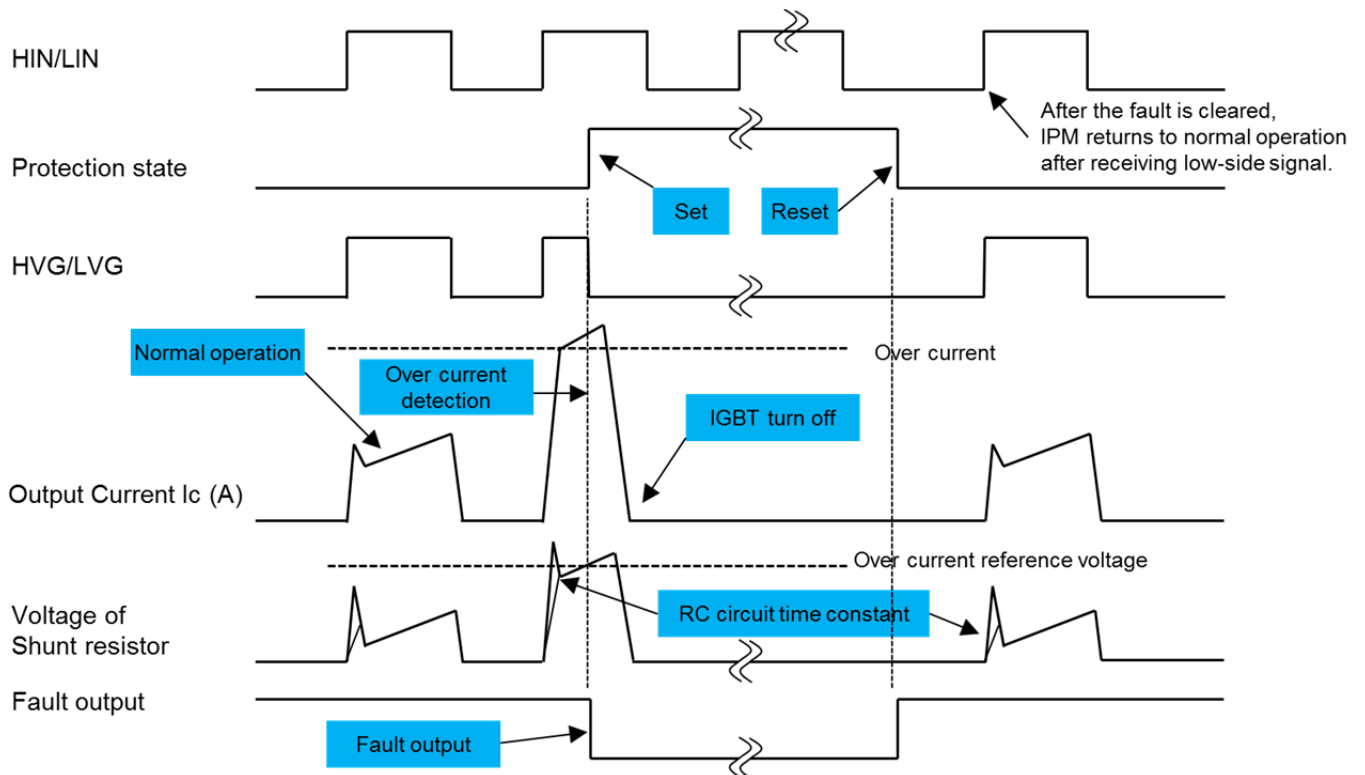


Figure 11. Overcurrent Protection Timing Diagram

## 4.2. Under Voltage Lockout Protection

The UVLO protection is designed to prevent unexpected operating behavior as described in Table 4. Both High-side and Low-side have undervoltage protection. The low-side UVLO condition is indicated on the FAULT output. During the low-side UVLO state the FAULT output is continuously driven low. A high-side UVLO condition is not indicated on the FAULT output.

VDD Voltage (typ. Value)	Operation behavior
< 12.5V	As the voltage is lower than the UVLO threshold the control circuit is not fully turned on. A perfect functionality cannot be guaranteed.
12.5 V – 13.5 V	IGBTs can work, however conduction and switching losses increase due to low voltage gate signal.
13.5 V – 16.5 V	Recommended conditions
16.5 V – 20.0 V	IGBTs can work. Switching speed is faster and saturation current higher, increasing short-circuit broken risk.
> 20.0 V	Control circuit is destroyed. Absolute max. rating is 20 V.

Table 4. Module Operation according to VDD Voltage

The sequence of events in case of a low-side UVLO event (IGBTs turned off and active fault output) is shown in Figure 12. Figure 13 shows the same for a high-side UVLO (IGBTs turned off but no fault output).

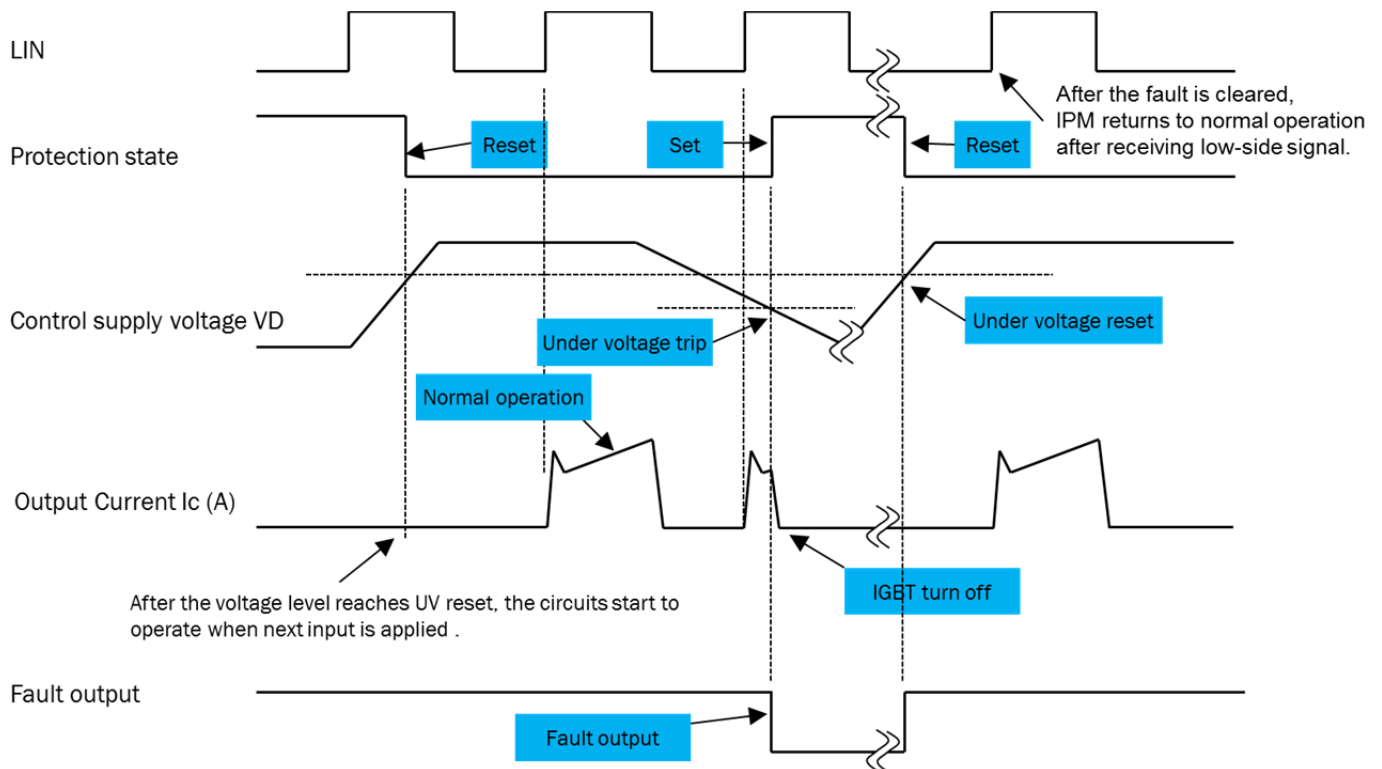


Figure 12. Low-side UVLO Timing Diagram

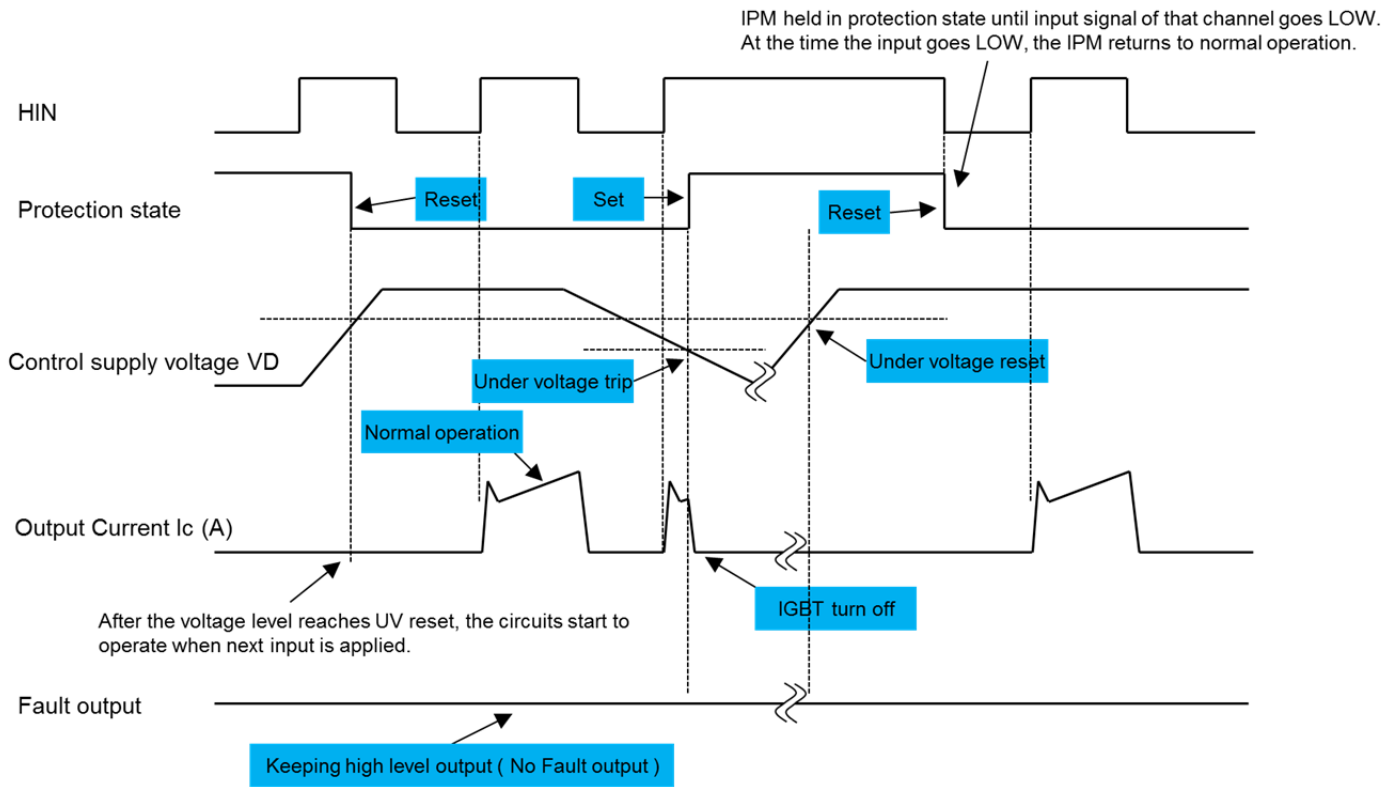


Figure 13. High-side UVLO Timing Diagram

### 4.3. Cross-conduction prevention

The Compact IPM series implements cross-conduction prevention logic at the gate driver to avoid simultaneous drive of the low-side and high-side IGBTs as shown in Figure 14.

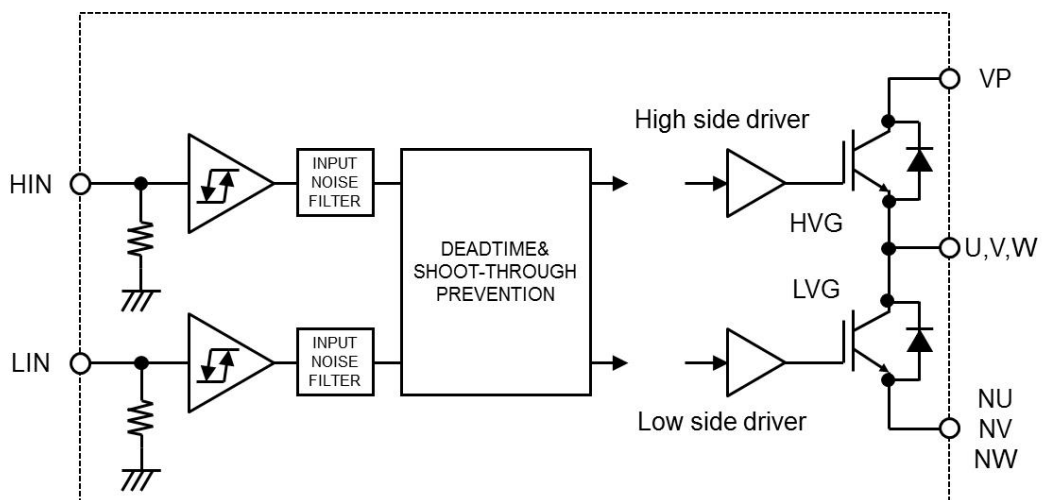


Figure 14. Cross-conduction Prevention

If both high-side and low-side drive inputs are active (HIGH) the logic prevents both gates from being driven as shown in Figure 15 below.

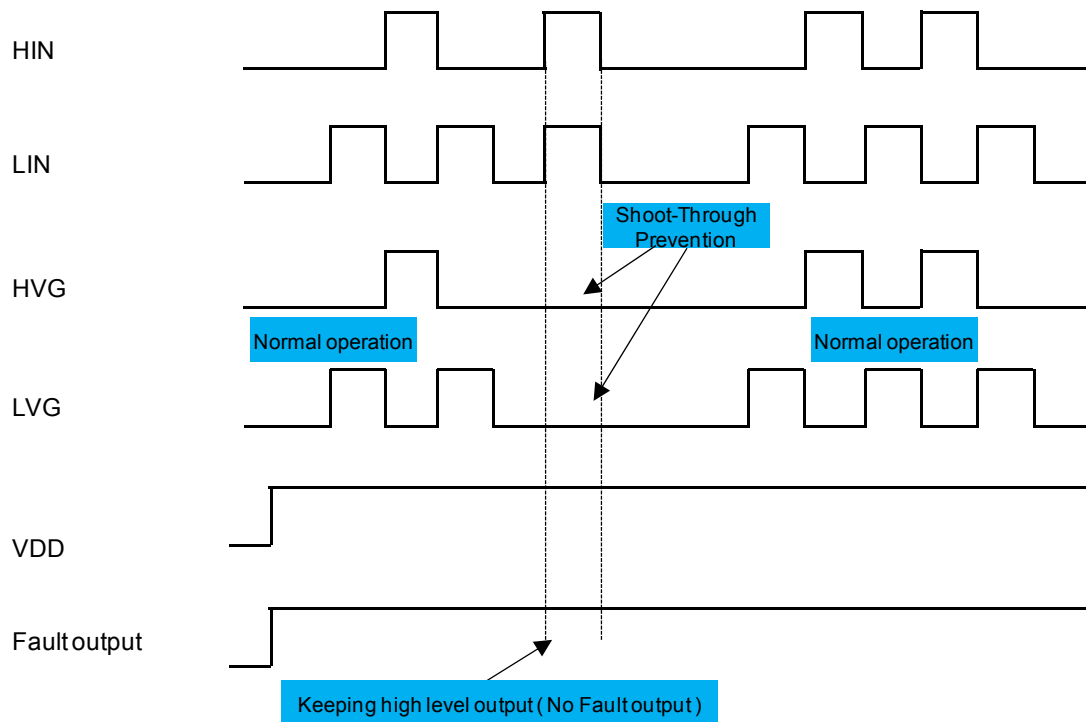


Figure 15. Cross-conduction Prevention Timing Diagram

Even if cross-conduction on the IGBTs due to incorrect external driving signals is prevented by the circuitry, the driving signals (HIN and LIN) need to include a “dead time”. This period where both inputs are inactive between either one becoming active is required due to the internal delays within the IGBTs.

Figure 16 shows the delay from the HIN-input via the internal high-side gate driver to high-side IGBT, the delay from the LIN-input via the internal low-side gate driver to low-side IGBT and the resulting minimum dead time which is equal to the potential shoot through period:

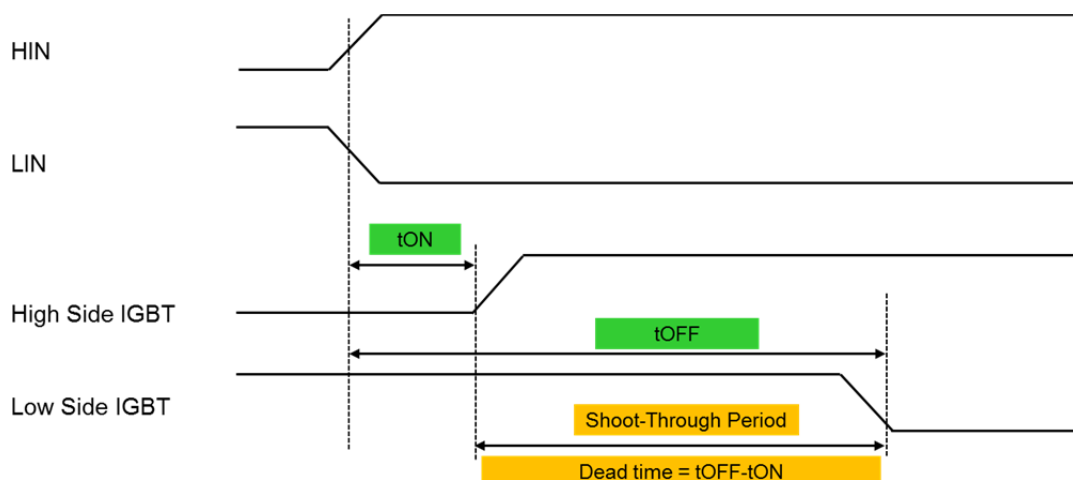


Figure 16. Shoot-through Period

## 5. PCB design and mounting guidelines

This chapter provides guidelines for an optimized design and PCB layout as well as module mounting recommendations to appropriately handle and assemble the IPM.

### 5.1. Application (schematic) design

Figure 17 gives an overview of the external components and circuits when designing with the Compact IPM series modules.

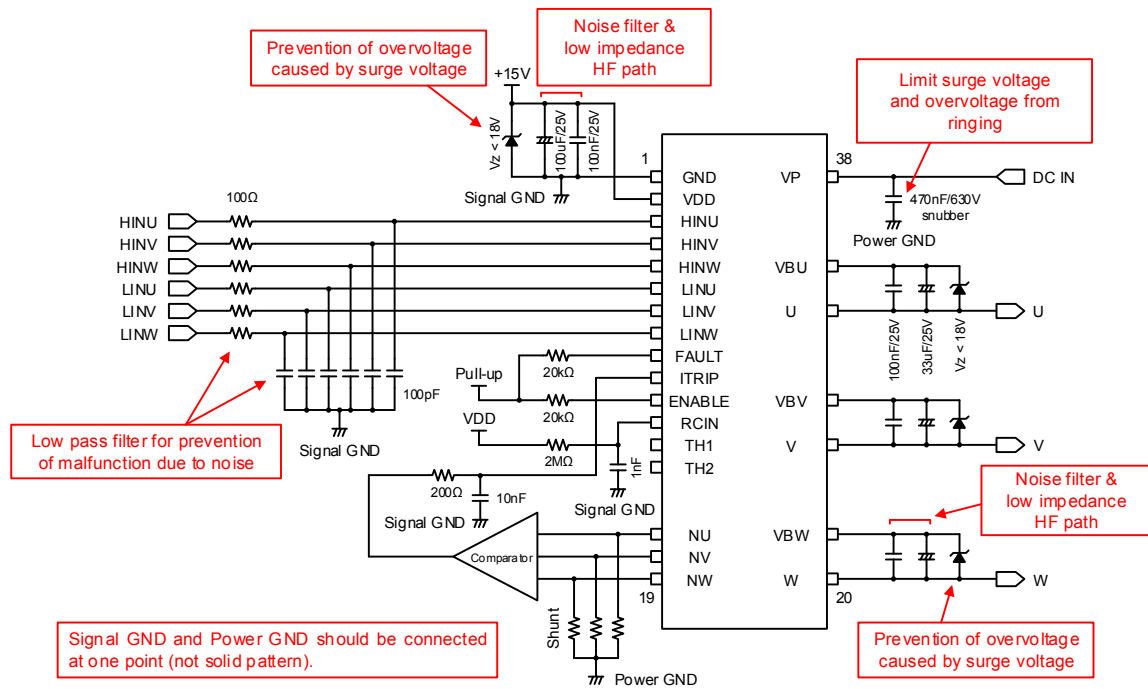


Figure 17. Compact IPM series application circuit

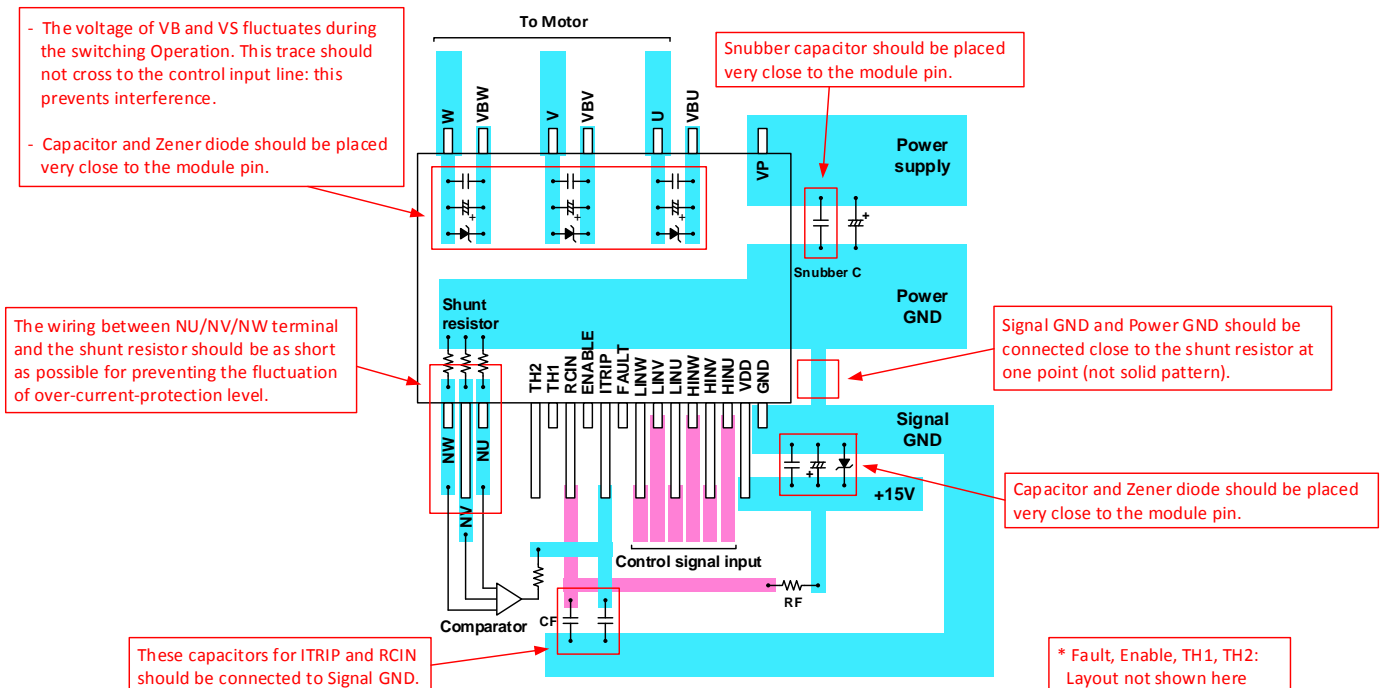


Figure 18. Compact IPM recommended layout

## 5.2. Pin by pin design and usage notes

This section provides pin by pin PCB layout recommendations and usage notes. A complete list of module pins is given in Chapter 6.

<b>VP</b> <b>NU, NV, NW</b>	DC Power supply terminal for the inverter block. Voltage spikes could be caused by longer traces to these terminals due to the trace inductance, therefore traces are recommended to be as short as possible. In addition a snubber capacitor should be connected as close as possible to the VP terminal to stabilize the voltage and absorb voltage surges.
<b>U, V, W</b>	These are the output pins for connecting the 3-phase motor. They share the same GND potential with each of the high-side control power supplies. Therefore they are also used to connect the GND of the bootstrap capacitors. These bootstrap capacitors should be placed as close to the module as possible.
<b>VDD, GND</b>	These pins provide power to the low-side gate drivers, the protection circuits and the bootstrap circuits. The voltage between these terminals is monitored by the UVLO circuit. The GND terminal is the reference voltage for the input control signals.
<b>VBU, VBV</b> <b>VBW</b>	The VBx pins are internally connected to the positive supply of the high-side drivers. The supply needs to be floating and electrically isolated. The boot-strap circuit shown in Figure 19 forms this power supply individually for every phase. Due to integrated boot FET only an external boot capacitor (CB) is required.

CB is charged when the following two conditions are met.

- ① Low-side signal is input
- ② Motor terminal voltage is low level

The capacitor is discharged while the high-side driver is activated.

Thus CB needs to be selected taking the maximum on time of the high-side and the switching frequency into account.

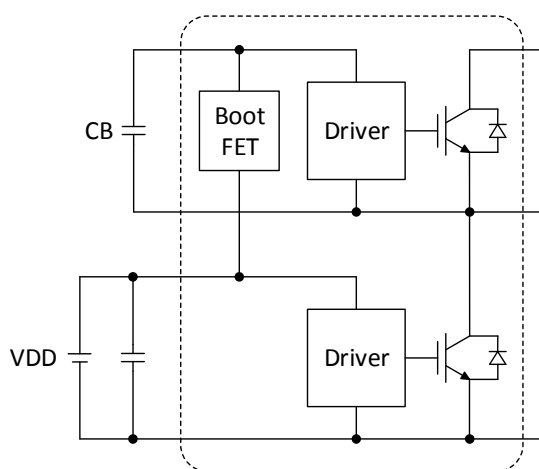


Figure 19. Bootstrap Circuit

The voltages on the high-side drivers are individually monitored by the under voltage protection circuit. If there is a UVLO fault on any given phase, the output on that phase is disabled.

Typically a CB value of less or equal 47uF ( $\pm 20\%$ ) is used. In case the CB value needs to be higher, an external resistor (20 $\Omega$  or less) should be used in series with the capacitor to avoid high currents which can cause malfunction of the IPM.

**HINU, LINU  
HINV, LINV  
HINW,  
LINW**

These pins are the control inputs for the power stages. The inputs on HINU/HINV/HINW control the high-side transistors of U/V/W, the inputs on LINU/LINV/LINW control the low-side transistors of U/V/W respectively. The input logic is active HIGH. An external microcontroller can directly drive these inputs without need for isolation

Simultaneous activation of both low-side and high-side is prevented internally to avoid shoot through at the power stage. However, due to IGBT switching delays the control signals must include a dead-time.

The equivalent input stage circuit is shown in Figure 20.

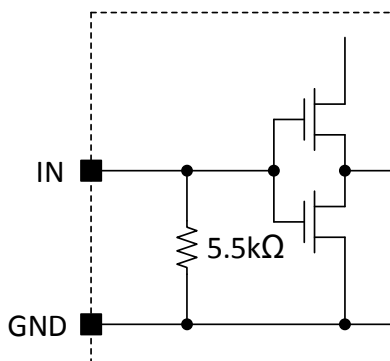


Figure 20. Internal Input Circuit

The output might not respond when the width of the input pulse is less than 1 $\mu$ s (both ON and OFF).

Note: After applying VDD, it is necessary to input the low-side signal for starting the operation.

**FAULT**

The Fault pin is an active low output (open-drain output). It is used to indicate an internal fault condition of the module. The structure is shown in Figure 21.

The sink current of IoSD during an active fault is nominal 2mA @ 0.1V. Depending on the interface supply voltage, the external pull-up resistor (RP) needs to be selected to set the low voltage below the VIL trip level.

*For the commonly used supplies :*

*Pull up voltage = 15V ->  $R_P \geq 20k\Omega$*

*Pull up voltage = 5V ->  $R_P \geq 6.8k\Omega$*

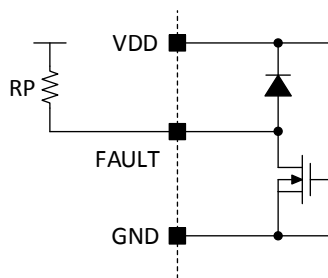


Figure 21. Fault Connection

For a detailed description of the fault operation refer to Chapter 4.

Note: The Fault signal does not permanently latch. After the protection event ended, and the fault clear time(1.65ms) passed, the module's operation is re-started by inputting the low-side signal. Therefore the input needs to be driven low externally activated as soon as a fault is detected.

**ITRIP** This pin is used to enable an OCP function. When the voltage of this pin exceeds a reference voltage, the OCP function operates. For details of the OCP operation refer to Chapter 4.

**ENABLE** Enable pin has shutdown function of the internal gate driver. The gate driver operates when the voltage of this pin is at 2.5V or more, and stops at 0.8V or less. This pin can also be connected to the FAULT pin directly.

**TH1,TH2** An internal thermistor to sense the substrate temperature is connected between TH1 and TH2. By connecting an external pull-up resistor to either of TH1 and TH2, and shorting the other and GND, the module temperature can be monitored. Please refer to heading 3.2 for details of the thermistor.

Note: This is the only means to monitor the substrate temperature indirectly.

**RCIN** This pin is used to set the fault clear time.

#### STK5Q4U3xxJ series

By connecting the resistor  $R_F$  versus VDD and the capacitor  $C_F$  versus GND, the fault clear time can be set. In condition that  $R_F$  is  $2M\Omega$  and  $C_F$  is  $1nF$ , the fault clear time is 1.65ms.

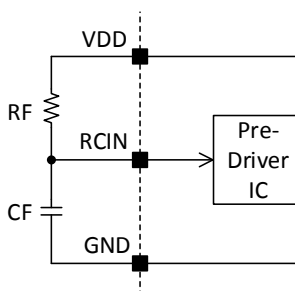


Figure 22. RCIN circuit (STK5Q4U3xxJ series)

To shorten the fault clear time, reduce the value of  $R_F$  or  $C_F$ .

STK5C4U332J-E

The resistor and the capacitor for setting the fault clear time are built-in as shown in Figure 23. It is recommended to leave this pin open. In that case, the default fault clear time is 2ms.

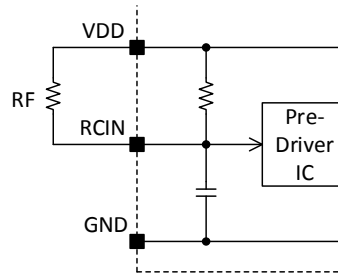


Figure 23. RCIN circuit (STK5C4U332J-E)

To shorten the fault clear time, connect an external resistor RF between VDD and RCIN.

### 5.3. Heat sink mounting and torque

If a heat sink is used, insufficiently secure or inappropriate mounting can lead to a failure of the heat sink to dissipate heat adequately.

The following general points should be observed when mounting IPM on a heat sink:

1. Verify the following points related to the heat sink:
  - There must be no burrs on aluminum or copper heat sinks.
  - Screw holes must be countersunk.
  - There must be no unevenness in the heat sink surface that contacts IPM.
  - There must be no contamination on the heat sink surface that contacts IPM.
2. Highly thermal conductive silicone grease needs to be applied to the whole back (aluminum substrate side) uniformly, and mount IPM on a heat sink. If the device is removed, grease must be applied again.
3. For a good contact between the IPM and the heat sink, the mounting screws should be tightened gradually and sequentially while a left/right balance in pressure is maintained. Either a bind head screw or a truss head screw is recommended. Please do not use tapping screw. We recommend using a flat washer in order to prevent slack.

The standard heat sink mounting condition of the Compact IPM series is as follows.

Item	Recommended Condition
Pitch	26.0±0.1mm (Please refer to Package Outline Diagram)
Screw	Diameter : M3 Screw head types: pan head, truss head, binding head
Washer	Plane washer dimensions D = 7mm, d = 3.2mm and t = 0.5mm JIS B 1256
Heat sink	Material: Aluminum or Copper Warpage (the surface that contacts IPM ) : -50 to 50 μm Screw holes must be countersunk. No contamination on the heat sink surface that contacts IPM.
Torque	Temporary tightening : 50 to 60 % of final tightening on first screw Temporary tightening : 50 to 60 % of final tightening on second screw Final tightening : 0.4 to 0.6Nm on first screw Final tightening : 0.4 to 0.6Nm on second screw
Grease	Silicone grease. Thickness : 50 to 100 μm Uniformly apply silicon grease to whole back. Thermal foils are only recommended after careful evaluation. Thickness, stiffness and compressibility parameters have a strong influence on performance.

Table 5. Heat Sink Mounting

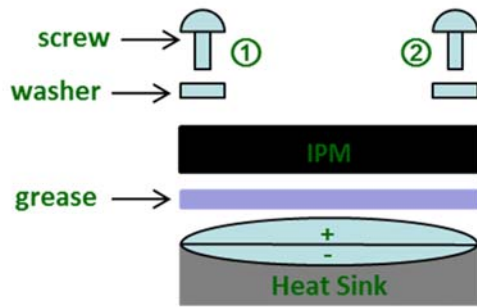


Figure 24. Mount IPM on a Heat Sink

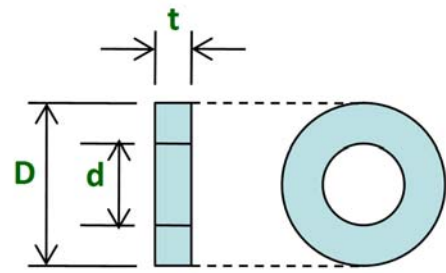


Figure 25. Size of Washer

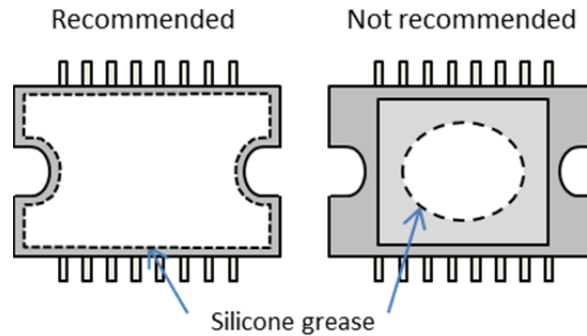


Figure 26. Uniform Application of Grease Recommended

Steps to mount an IPM on a heat sink

1st: Temporarily tighten maintaining a left/right balance.

2nd : Finally tighten maintaining a left/right balance.

#### 5.4. Mounting and PCB considerations

In designs in which the PCB and the heat sink are mounted to the chassis independently, use a mechanical design which avoids a gap between IPM and the heat sink, or which avoids stress to the lead frame of IPM by an assembly that slipping IPM is forcibly fixed to the heat sink with a screw.

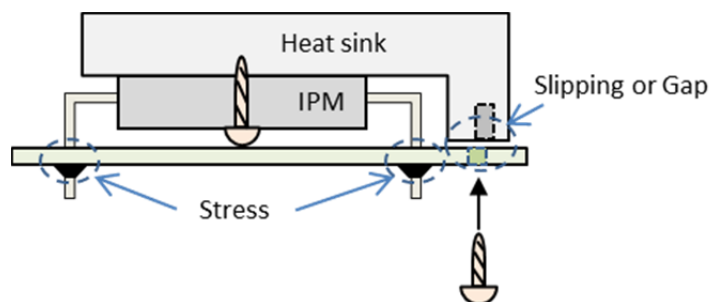
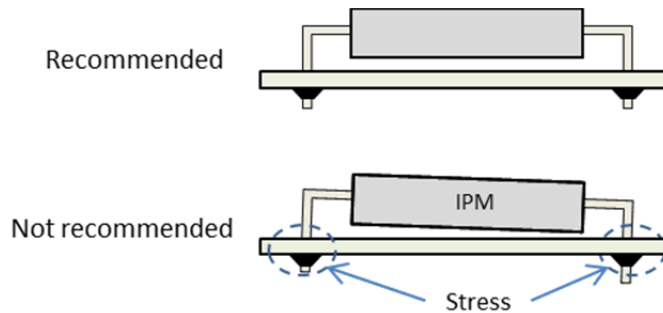


Figure 27. Fix to Heat Sink

Maintain a separation distance of at least 1.5 mm between the IPM case and the PCB. In particular, avoid mounting techniques in which the IPM substrate or case directly contacts the PCB.

Do not mount IPM with a tilted condition for PCB. This can result in stress being applied to the lead frame and IPM substrate could short out tracks on the PCB. If stress is given by compulsory correction of a lead frame after the mounting, a lead frame may drop out.



Since the use of sockets to mount IPM can result in poor contact with IPM leads, we strongly recommend making direct connections to PCB.

#### Mounting on a PCB

1. Align the lead frame with the holes in the PCB and do not use excessive force when inserting the pins into the PCB. To avoid bending the lead frames, do not try to force pins into the PCB unreasonably.
2. Do not insert IPM into PCB with an incorrect orientation, i.e. be sure to prevent reverse insertion. IPMs may be destroyed or suffer a reduction in their operating lifetime by this mistake.
3. Do not bend the lead frame.

#### 5.5. Cleaning

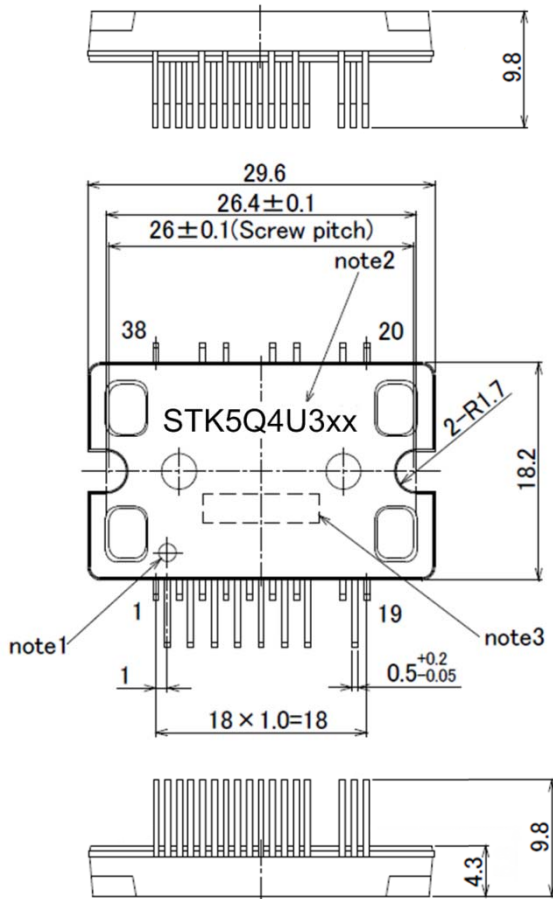
IPM has a structure that is unable to withstand cleaning. Do not clean independent IPM or PCBs on which an IPM is mounted.

## 6. Package Outline

The package of STK5Q4U3xxJ series is DIP33 shown in Figure 28.  
The package of STK5C4U332J-E is DIP33 shown in Figure 29.

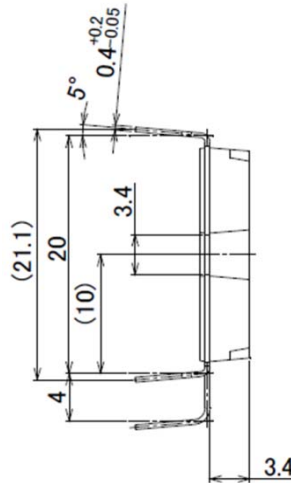
### 6.1. Package outline and dimension

#### STK5Q4U3xxJ series (DIP33)



Unit: mm

missing pin: 15,16,21,23,24,25,27  
29,30,31,33,35,36,37



note1: No.1 pin identification mark

note2: Model number

note3: Lot code

\* The form of a character in this drawing differs from that of IPM.

Figure 28. DIP33 Package Outline

STK5C4U332J-E (DIPS)

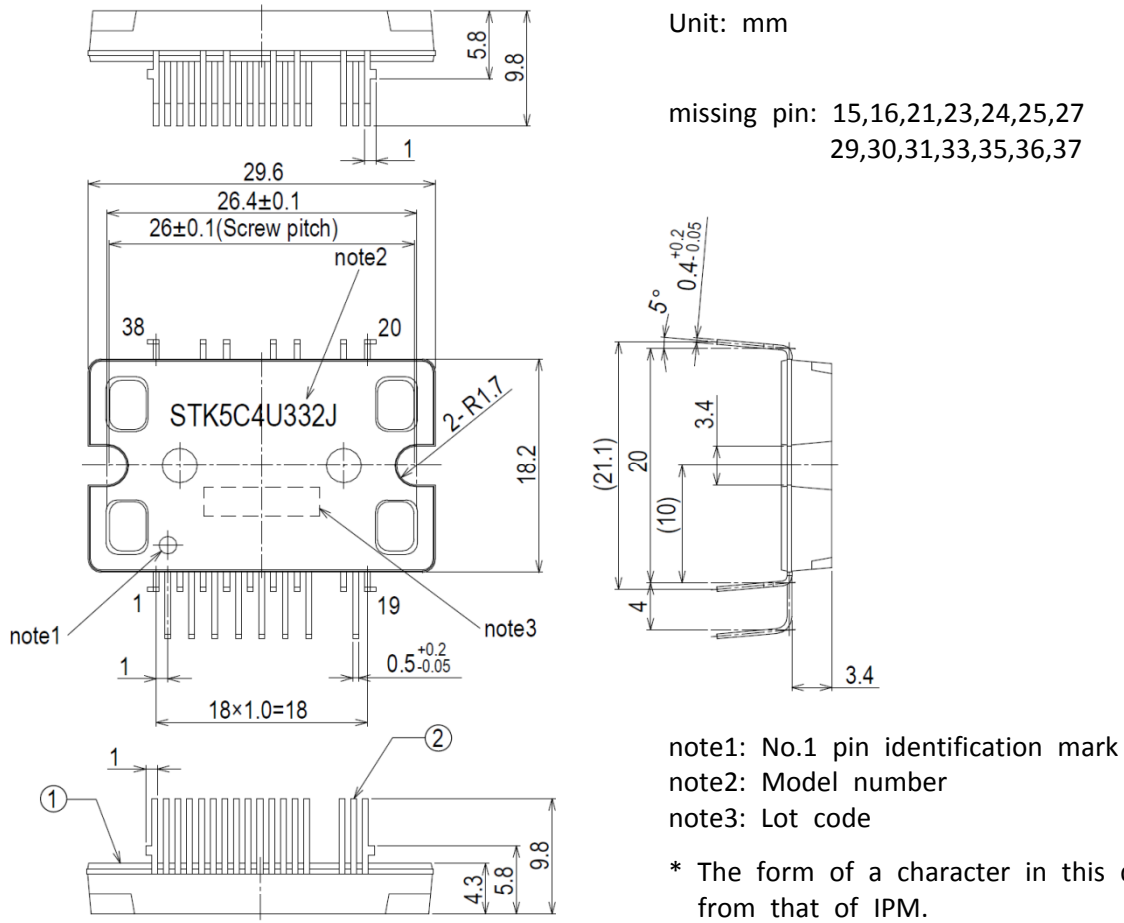


Figure 29. DIPS Package Outline

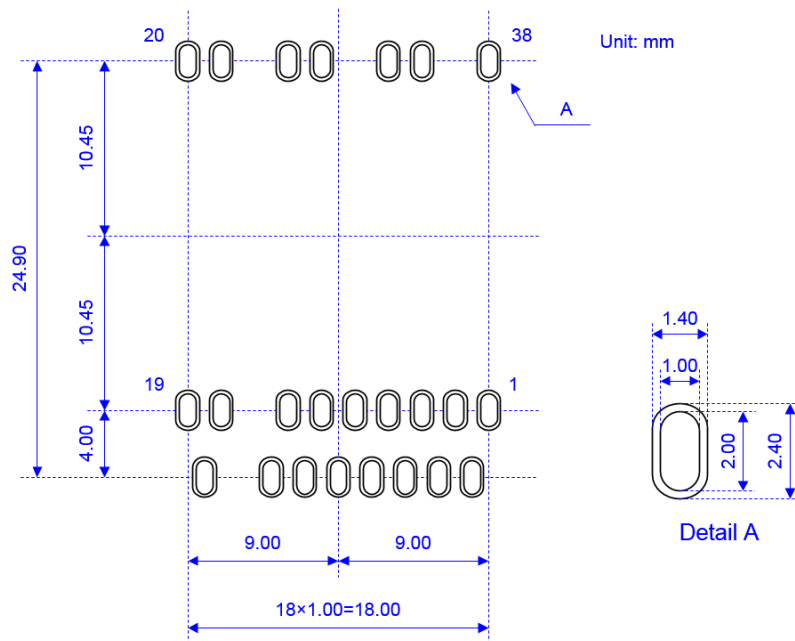


Figure 30. Recommended Land Pattern

## 6.2. Pin Out Description

Pin	Name	Description
1	GND	Negative Main Power Supply
2	VDD	+15V Main Power Supply
3	HINU	Logic Input for High-side Gate Driver - Phase U
4	HINV	Logic Input for High-side Gate Driver - Phase V
5	HINW	Logic Input for High-side Gate Driver - Phase W
6	LINU	Logic Input for Low-side Gate Driver - Phase U
7	LINV	Logic Input for Low-side Gate Driver - Phase V
8	LINW	Logic Input for Low-side Gate Driver - Phase W
9	FAULT	Fault Output
10	ITRIP	Shut Down Input
11	ENABLE	Enable Input
12	RCIN	Fault Clear Time Setting
13	TH1	Thermistor
14	TH2	Thermistor
17	NU	Low-side Emitter Connection - Phase U
18	NV	Low-side Emitter Connection - Phase V
19	NW	Low-side Emitter Connection - Phase W
20	W	Phase W Output / High-side Floating Supply Offset Voltage
22	VBW	High-side Floating Supply Voltage - Phase W
26	V	Phase V Output / High-side Floating Supply Offset Voltage
28	VBV	High-side Floating Supply Voltage - Phase V
32	U	Phase U Output / High-side Floating Supply Offset Voltage
34	VBU	High-side Floating Supply Voltage - Phase U
38	VP	Positive Bus Input Voltage

Note: Pins 15, 16, 21, 23, 24, 25, 27, 29, 30, 31, 33, 35, 36, 37 are not present.

## 7. Evaluation Board

The evaluation board consists of the minimum required components such as snubber capacitor and bootstrap circuit elements of the Compact IPM series.

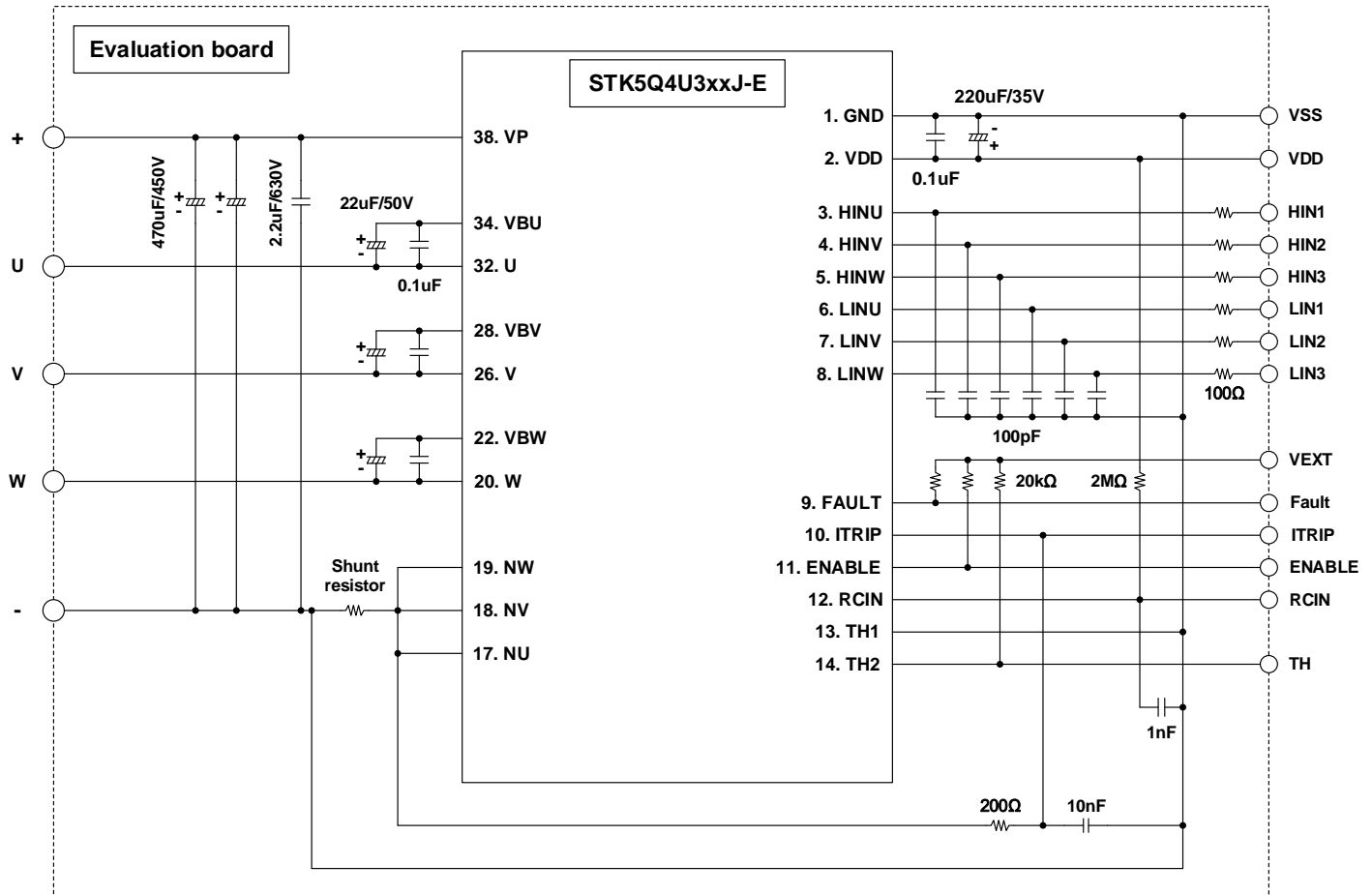
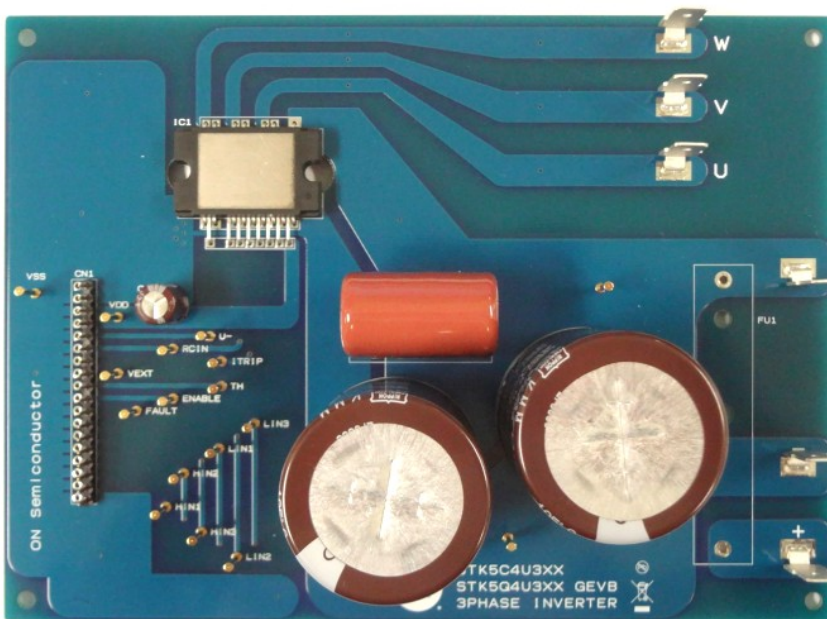


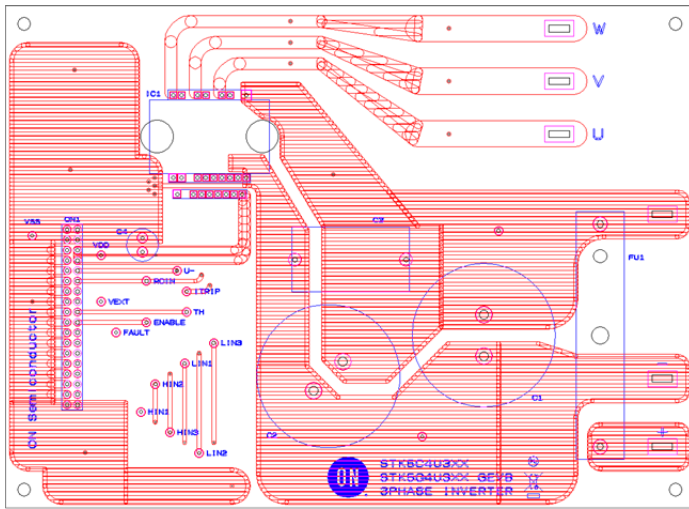
Figure 31. Evaluation Board Schematic



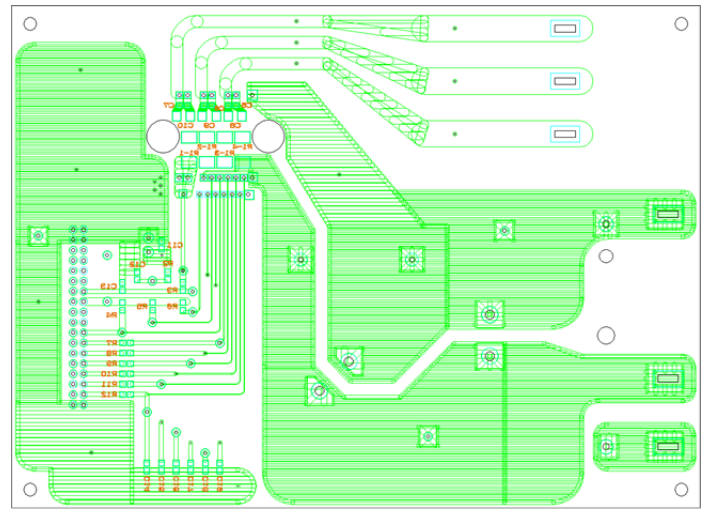
Length : 124mm  
Side : 170mm  
Thickness : 1.6mm

Rigid double-sided substrate  
Material : FR-4  
Copper foil thickness : 70um  
Both sides with resist coating

Figure 32. Photo of Evaluation Board



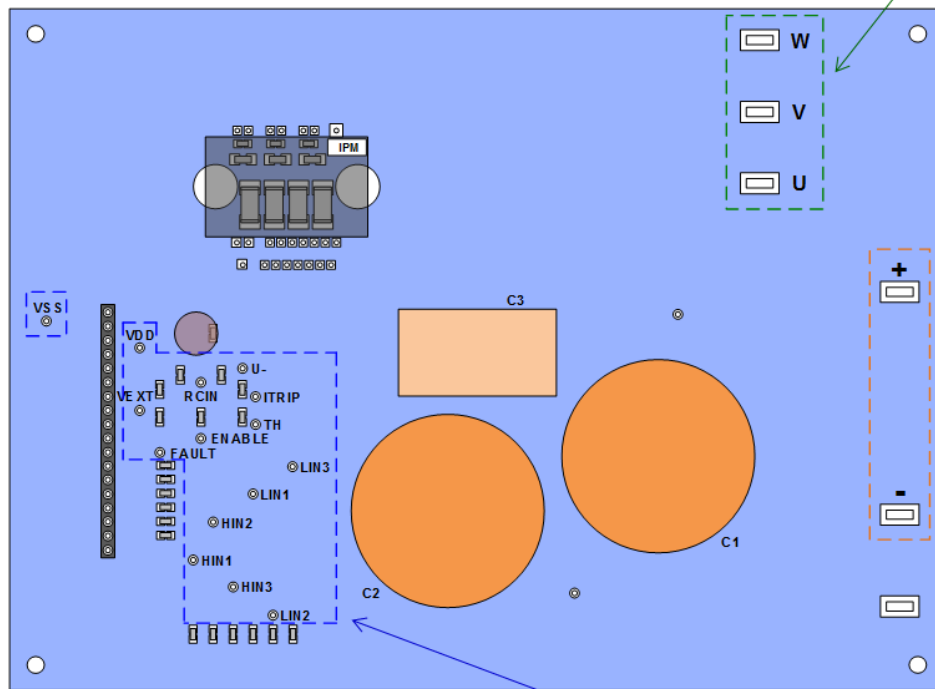
Top side



Back side

Figure 33. PCB Layout (TOP view)

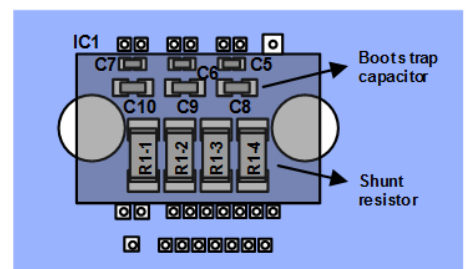
TOP view



**Green frame : U, V, W terminal**  
Please connect to the motor.

**Orange frame : +, - terminal**  
Please connect to DC power supply.

Enlarged view around IPM



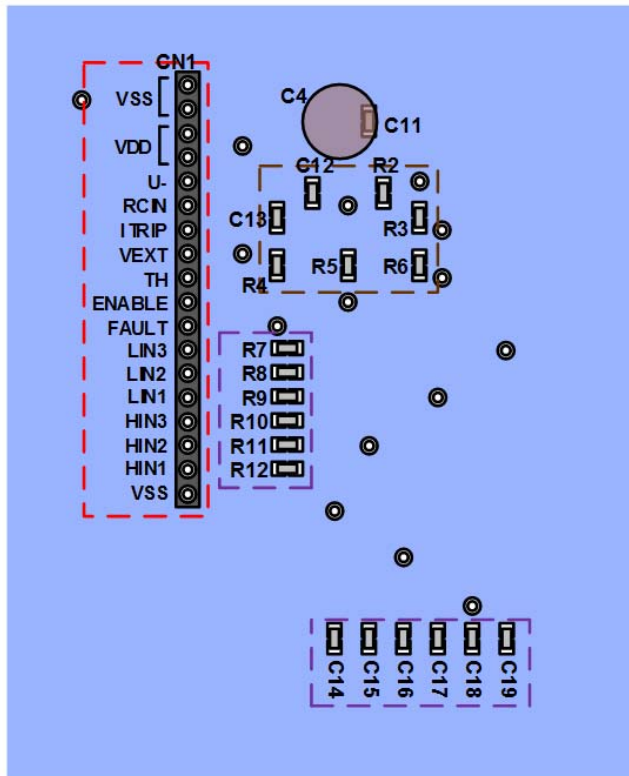
\* All chip components are mounted on solder side.

**Blue frame : Test pins**  
For monitoring each control signal

\* Shunt resistors are connected in series.

Figure 34. Description of each Pin ( figure 1 of 2)

Enlarged view around test pins



\* All chip components are mounted on solder side.

**Red frame : Connector**

For the connection to the control part

Vext terminal is connected pull-up resistor for TH, FAULT and ENABLE pins. Microcontroller I/O voltage should be connected to Vext.

**Purple frame : Low pass filter for signal input pins**

Resistor R7-R12 : 100Ω

Capacitor C14-C19 to VSS : 100pF

**Brown frame :**

R4, R5, R6 : Pull-up resistor to VEXT

R2, C12 : Fault clear time setting

R3, C13 : Time constant setting for ITRIP

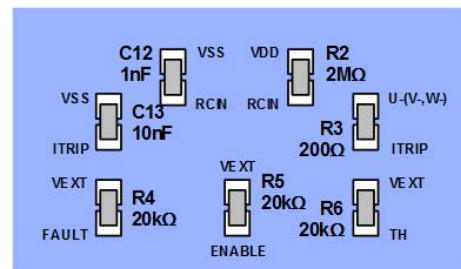


Figure 35. Description of each Pin ( figure 2 of 2)

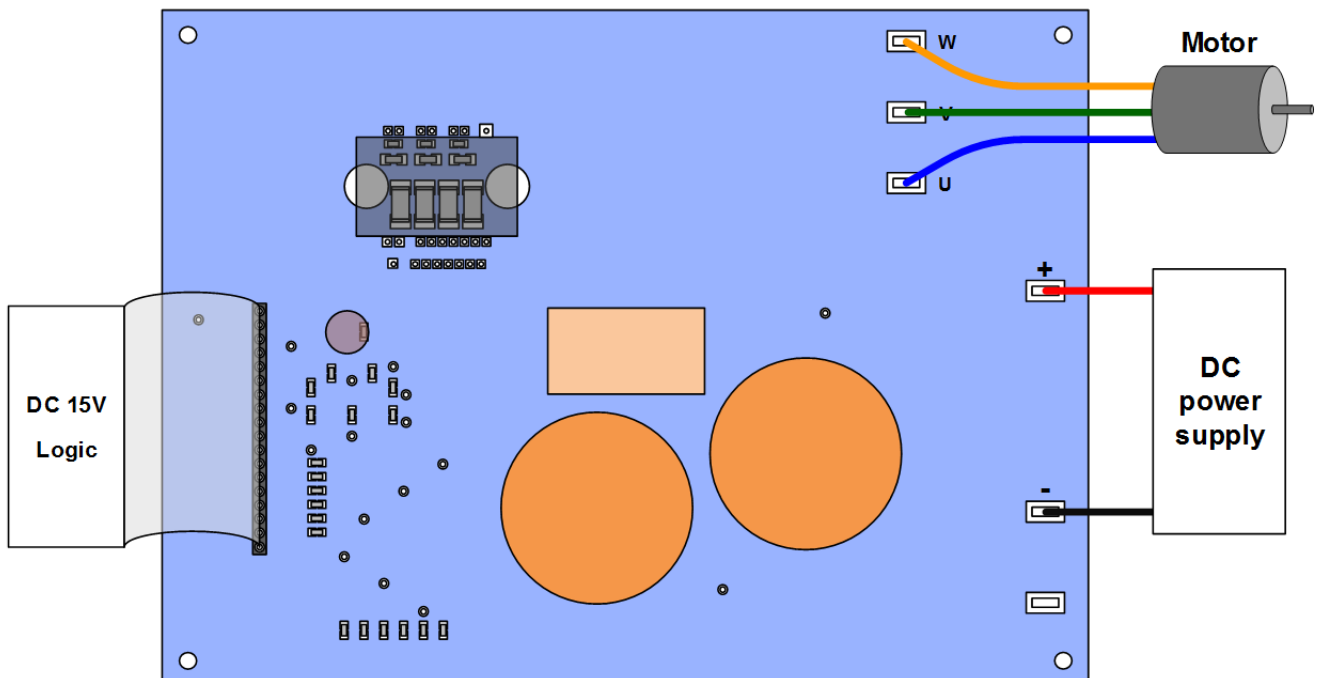


Figure 36. Connection Example

## Operating procedure

- Step1:** Connect IPM, the three power supplies, logic parts, inductor and the motor to the evaluation board, and confirm that each power supply is OFF at this time.
- Step2:** Apply DC15V to VDD and the logic I/O voltage to VEXT.
- Step3:** Perform a voltage setup according to specifications, and apply HV DC power supply between “+” and “-”.
- Step4:** The IPM will start when signals are applied. The low-side inputs must be switched on first to charge up the bootstrap capacitors.

**Note :** When turning off the power supply part and the logic part, please carry out in the reverse order to above steps.

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